HALOGEN

FREE



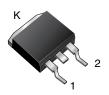
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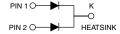
Dual Common Cathode Schottky Rectifier

High Barrier Technology for Improved High Temperature Performance

D²PAK (TO-263AB)



MBRB30HxxCT



PRIMARY CHARACTERISTICS					
I _{F(AV)}	2 x 15 A				
V_{RRM}	45 V, 60 V				
I _{FSM}	150 A				
V _F	0.56 V, 0.59 V				
I _R	80 μΑ, 60 μΑ				
T _J max.	175 °C				
Package	D ² PAK (TO-263AB)				
Circuit configuration	Common cathode				

FEATURES

- Power pack
- · Guardring for overvoltage protection
- Lower power losses, high efficiency
- Low forward voltage drop
- · Low leakage current
- High forward surge capability
- High frequency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- AEC-Q101 qualified available
- Automotive ordering code: base P/NHM3
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

For use in low voltage, high frequency rectifier of switching mode power supplies, freewheeling diodes, DC/DC converters, or polarity protection application.

MECHANICAL DATA

Case: D²PAK (TO-263AB)

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - RoHS-compliant, halogen-free, commercial grade

Base P/NHM3 - RoHS-compliant, halogen-free, AEC-Q101 qualified

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

M3 suffix meets JESD 201 class 1A whisker test, HM3 suffix meets JESD 201 class 2 whisker test

Polarity: as marked

MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)							
PARAMETER		MBRB30H45CT MBRB30H600		UNIT			
Maximum repetitive peak reverse voltage	V_{RRM}	45	60	V			
Working peak reverse voltage	V_{RWM}	45	60	V			
Maximum DC blocking voltage	V_{DC}	45	60	V			
Maximum average forward rectified current (fig. 1) total device	30		0	Α			
per diode	I _{F(AV)}	1	А				
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I _{FSM}	150		Α			
Peak repetitive reverse surge current per diode at t _p = 2 μs, 1 kHz	I _{RRM}	1.0	0.5	Α			
Peak non-repetitive reverse energy (8/20 μs waveform)		E _{RSM} 25 20		mJ			
Non-repetitive avalanche energy per diode at 25 °C, $I_{AS} = 4 A$, $L = 10 \text{ mH}$	E _{AS}	E _{AS} 80		mJ			
Electrostatic discharge capacitor voltage human body model: C = 100 pF, R = 1.5 $k\Omega$	V _C	25		kV			
Voltage rate of change (rated V _R)	dV/dt 10 000		V/µs				
Operating junction and storage temperature range	T _J , T _{STG}	-65 to	°C				



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ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)								
PARAMETER	TEST CONDITIONS		SYMBOL	MBRB30H45CT		MBRB30H60CT		UNIT
PARAMETER	1231 00	DIVIDITIONS	JN3 STWIBOL		TYP. MAX. TYP.		MAX.	ONII
Maximum instantaneous forward voltage per diode	I _F = 15 A	T _C = 25 °C	V _F ⁽¹⁾	-	0.62	ı	0.68	v
	I _F = 15 A	T _C = 125 °C		0.49	0.56	0.55	0.59	
	I _F = 30 A	T _C = 25 °C		-	0.73	ı	0.83	V
	I _F = 30 A	T _C = 125 °C		0.62	0.67	0.68	0.71	
Maximum reverse current per diode at working peak reverse voltage		T _J = 25 °C	I _R ⁽²⁾	-	80	1	60	μΑ
		T _J = 125 °C		5.0	15	4.0	15	mA

Notes

 $^{(1)}\,$ Pulse test: 300 μs pulse width, 1 $\,\%$ duty cycle

(2) Pulse test: pulse width \leq 40 ms

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	MBRB30H45CT MBRB30H60CT		UNIT	
Typical thermal resistance junction to case per diode	$R_{ heta JC}$	1.5		°C/W	

ORDERING INFORMATION (Example)							
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
D ² PAK (TO-263AB)	MBRB30H45CT-M3/I	1.35	I	800/reel	Tape and reel		
D ² PAK (TO-263AB)	MBRB30H45CTHM3/I (1)	1.35	I	800/reel	Tape and reel		

Notes

(1) AEC-Q101 qualified

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RATINGS AND CHARACTERISTICS CURVES (T_A = 25 °C unless otherwise noted)

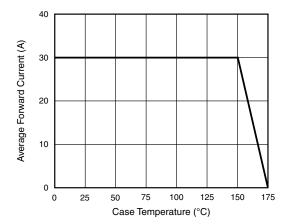


Fig. 1 - Forward Derating Curve

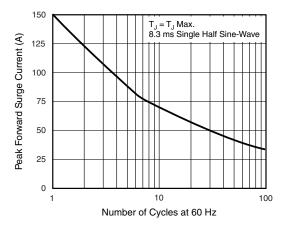


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current Per Diode

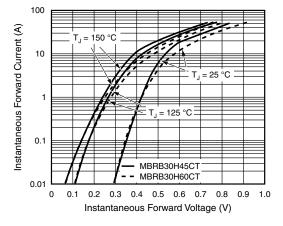


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

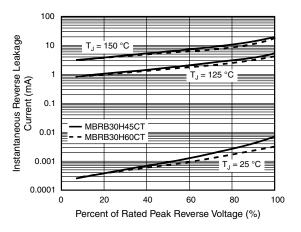


Fig. 4 - Typical Reverse Characteristics Per Diode

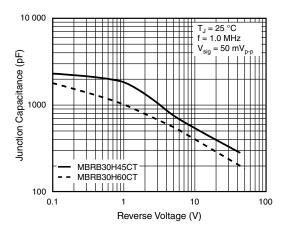


Fig. 5 - Typical Junction Capacitance Per Diode

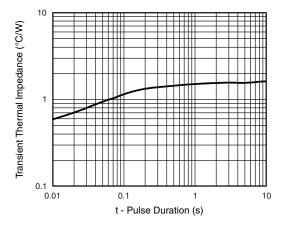


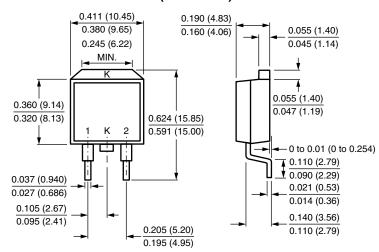
Fig. 6 - Typical Transient Thermal Impedance Per Diode



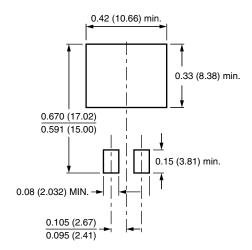
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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

D²PAK (TO-263AB)



Mounting Pad Layout





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